

Silicon NPN Power Transistors

2SD849

DESCRIPTION

- With TO-3 package
- High voltage ,high speed

APPLICATIONS

- Line-operated horizontal deflection output applications

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

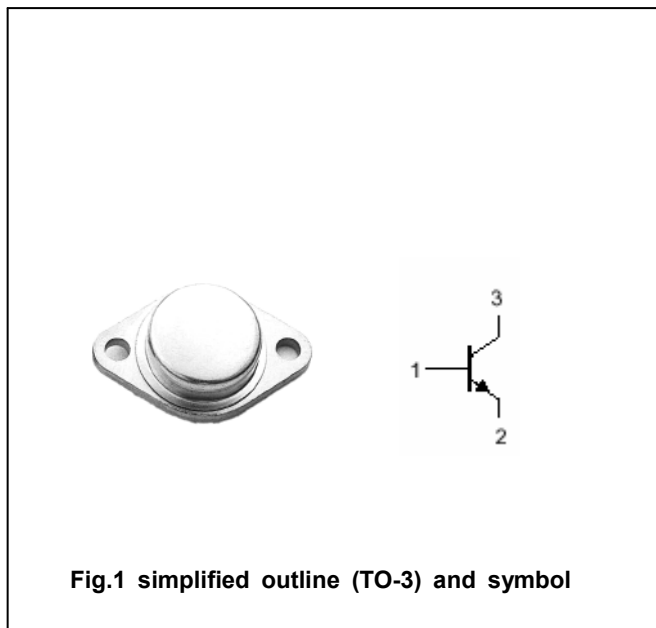


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	600	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		3	A
I_{CM}	Collector current-peak		5	A
P_T	Total power dissipation	$T_C = 90 \square$	25	W
T_j	Junction temperature		150	\square
T_{stg}	Storage temperature		-65~150	\square

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =0.1A; I _B =0	600			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10mA; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =3 A; I _B =1A			5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =3 A; I _B =1A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =750V; I _E =0			0.1	mA
		V _{CB} =1500V; I _E =0			1.0	
h _{FE-1}	DC current gain	I _C =0.5A ; V _{CE} =5V	8			
h _{FE-2}	DC current gain	I _C =3A ; V _{CE} =10V	4		12	
t _f	Fall time	I _C =3 A; I _{Bend} =1A; L _B =20μH			0.9	μs
t _s	Storage time			13		μs

PACKAGE OUTLINE



Fig.2 Outline dimensions